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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Toshiya UEMURA, et al.

Serial No.: 09/819,952

Group Art Unit: 2815

Filed: March 29, 2001

Examiner: Bradley W. Baumeister

For: LIGHT-EMITTING DEVICE USING GROUP III NITRIDE GROUP COMPOUND  
SEMICONDUCTOR AND METHOD FOR MANUFACTURING IT

Honorable Commissioner of Patents  
Washington, D.C. 20231

**AMENDMENT UNDER 37 C.F.R. § 1.111**

Sir:

In response to the Final Office Action dated September 5, 2002, please amend the  
above-identified application as follows:

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**IN THE CLAIMS:**

**Please amend the claims to read as follows:**

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1. (Amended) A light-emitting semiconductor device comprising:  
a substrate;  
a plurality of semiconductor layers which comprise group III nitride group compound  
semiconductors and are laminated on said substrate by crystal growth;  
an emission layer formed on a first side of the substrate; and  
a mirror surface formed on a second side of the substrate opposite the first side, said  
mirror surface comprising:  
a light transmission layer which directly contacts said substrate, has luminous  
transparency, and comprises at least one material selected from a group consisting of metal  
oxides and ceramics; and  
a reflection layer which is formed on said light transmission layer, comprises a  
metal, and reflects lights emitted from said emission layer.

2. (Amended) A light-emitting semiconductor device comprising: